

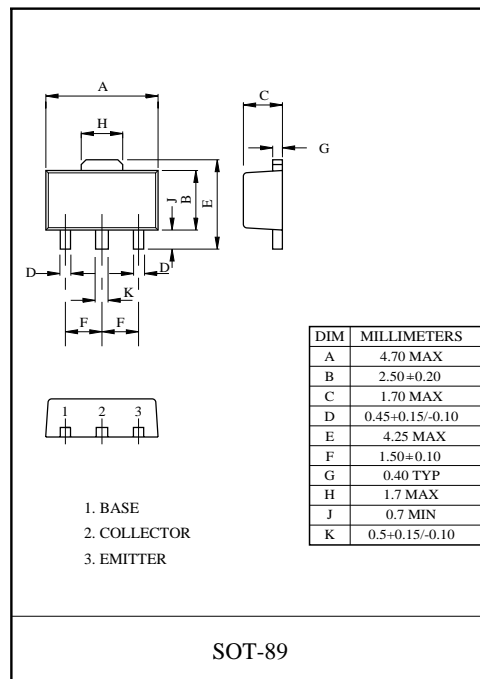
FTA1668 TRANSISTOR(PNP)

FEATURES

- High voltage: $V_{CE0} = -60V$
- High transistors frequency
- Complementary to FTC4378

MAXIMUM RATINGS ($T_a=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-80	V
V_{CEO}	Collector-Emmitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-1	A
P_C	Collector power dissipation	500	mW
T_J	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature	-55~150	$^\circ C$



ELECTRICAL CHARACTERISTICS ($T_a=25^\circ C$ unless otherwise specified)

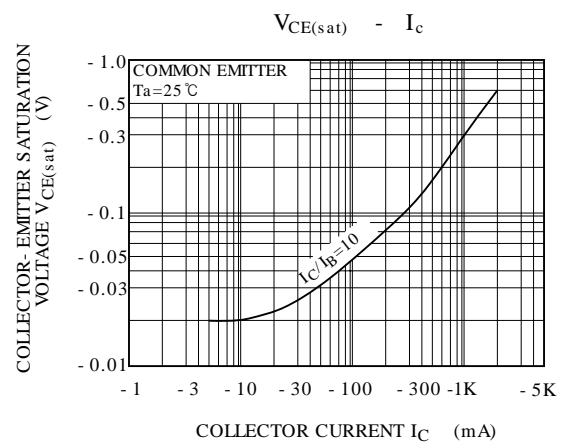
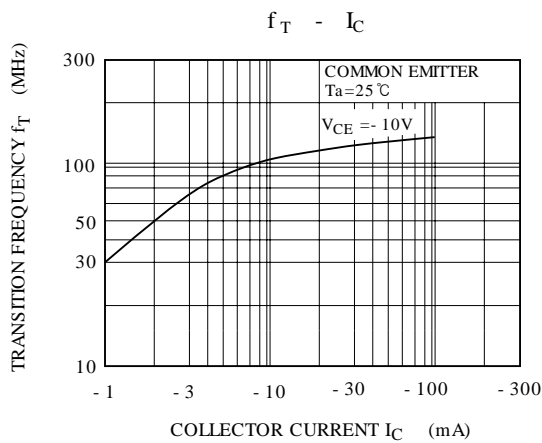
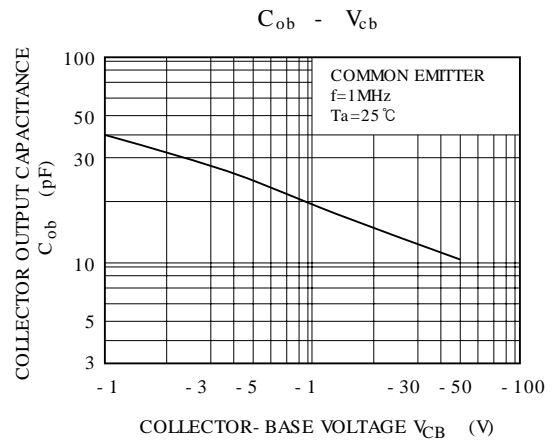
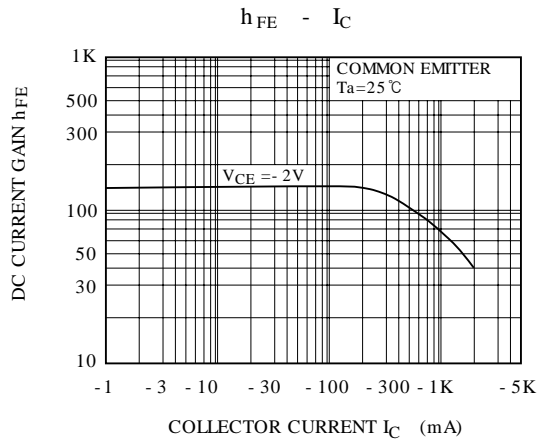
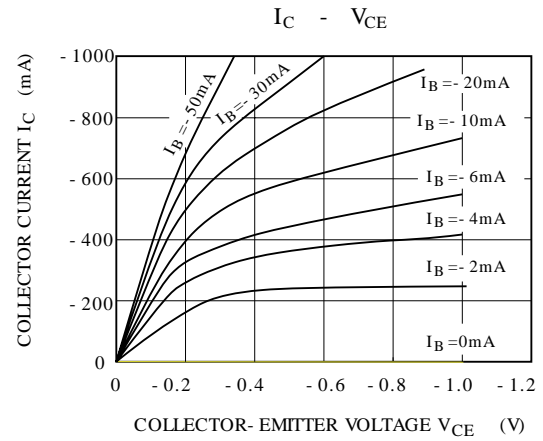
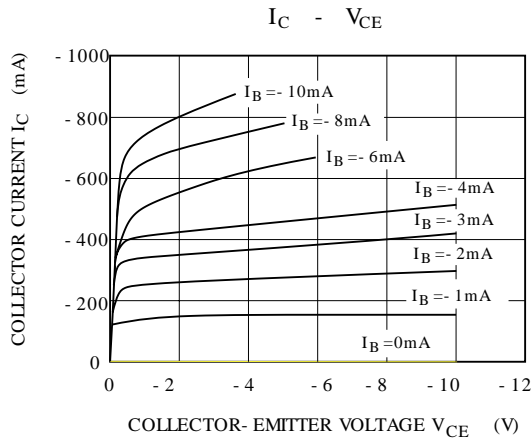
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-0.1mA, I_E=0$	-80			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-0.1mA, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-50V, I_E=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-4V, I_C=0$			-0.1	μA
DC current gain	h_{FE1}	$V_{CE}=-2V, I_C=-50mA$	60		320	
	h_{FE2}	$V_{CE}=-2V, I_C=-1A$	30			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-500mA, I_B=-50mA$			-0.7	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-500mA, I_B=-50mA$			-1.2	V
Transition frequency	f_T	$V_{CE}=-10V, I_C=-50mA, f=100MHz$		150		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$		12		pF

CLASSIFICATION of h_{FE1}

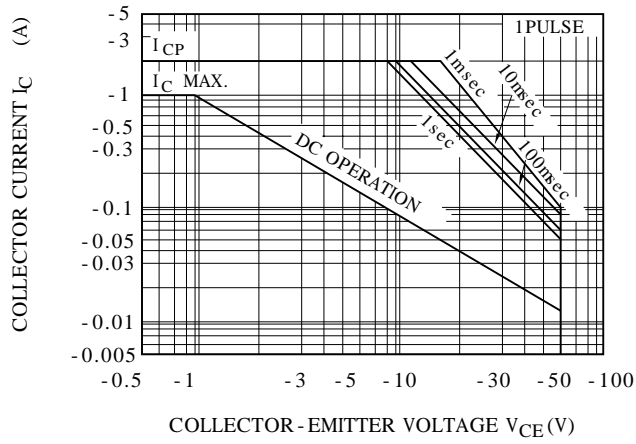
Rank	O	Y	GR
Range	60- 120	100- 240	160- 320
Marking	JO	JY	JGR



FTA1668



SAFE OPERATING AREA



$P_C - T_a$

